

**A LOW LOSS OPTICAL WAVEGUIDE, A METHOD OF ITS
MANUFACTURE AND AN OPTICAL DEVICE**

5 TECHNICAL FIELD

This invention relates to the manufacture of high quality optical films.

10 The invention relates specifically to an optical waveguide for guiding light in a predefined wavelength range, the optical waveguide comprising core and cladding regions for confining light, the core and/or cladding region or regions being formed on a substrate, and the whole or a part of the core and/or cladding region or regions comprising material of the stoichiometric composition $\text{Si}_a\text{O}_x\text{N}_y\text{X}_z\text{H}_v$.

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The invention furthermore relates to: A method of manufacturing an optical waveguide for guiding light in a predefined wavelength range, the optical waveguide comprising core and cladding regions for confining light, to an optical waveguide obtainable by the method and to an optical device
20 comprising an optical waveguide.

This invention can be applied to all types of optical devices based on index guiding waveguide layers as well as photonic band gap related waveguide technologies. The invention may e.g. be useful in applications such as
25 optical communication systems, in particular for branching components (e.g. splitters) and components for wavelength division multiplexing (WDM) systems, e.g. telecommunication systems, fibre-to-the-home-systems, etc.

30 BACKGROUND ART

It is well known that it is difficult to fabricate optically transparent silica based waveguides with sufficiently low losses over a broad range of wavelengths. The commercially mature planar glass on silicon waveguide technology is
35 typically based on low-index contrast (e.g. less than 0.7%), the index difference between core and cladding being calculated as:

$$(\Delta n / \langle n \rangle) \cdot 100\% = 100\% \cdot 2 \cdot (n_1 - n_2) / (n_1 + n_2).$$

- This more or less standard low-index technology platform ensures planar waveguide components with low propagation loss (< 0.05 dB/cm) and low fiber-to-chip coupling losses (e.g. < 0.3 dB/facet). The refractive index difference between the waveguide core and cladding is generally achieved by doping the silica core material with higher refractive index oxides such as germanium, phosphorous oxide, titanium oxide, etc., in order to raise the refractive index above that of the surrounding cladding.
- Increasing the index above 0.7% will allow for smaller bending radii without increasing the bending loss, and hence, smaller devices may be fabricated (cf. e.g. "A Low-Loss, compact wide-FSR-AWG using Planar Lightwave Circuit Technology", C. Doerr, FJ1 OFC 2003). This will allow for more devices per wafer, or alternatively create space for more complex components with higher functionalities. Higher index contrast will eventually also open up for devices which cannot be made at a lower index contrast such as planar devices utilising a photonic band gap (PBG) effect. Recent developments in the design and fabrication of visible PBG waveguide devices in Si_3N_4 type materials have been discussed extensively by M. D. B. Charlton, et al., J. of Materials Science: Materials in Electronics 10 (1999) p. 429-440 (and references herein).

- As a promising production platform for higher index waveguides, an oxynitride (SiO_xN_y) type of material has been discussed extensively in the literature. It has been known for a long time, and shown by several groups, that a SiO_xN_y type material can be fabricated with a tuneable refractive index which can be varied between that of SiO_2 (1.455) and that of Si_3N_4 (2.02) by conventional deposition techniques (such as chemical vapour deposition (CVD), plasma enhanced CVD (PECVD), atmospheric pressure CVD (APCVD) or low pressure CVD (LPCVD) processes, cf. e.g. "Reduction of hydrogen induced losses in PECVD- SiO_xN_y optical waveguides in the near infrared", H. Albers et al., in Proceedings of OFPW3.4, LEOS '95, IEEE Lasers and Electro-Optics Society 1995 Annual Meeting, 8th Annual Meeting. Although the high-end range of the refractive indices has been shown to have a high tendency for crack formation upon annealing to elevated temperatures, it has never the less been demonstrated that it is in

principle possible to tune the refractive index over the entire range, i.e. to achieve index differences from 0 % (SiO_2) to 32.5% (Si_3N_4).

However, from the literature it is also known that SiO_xN_y films will contain
5 Si:N-H bonds giving rise to an absorption peak at a wavelength $\lambda=1508$ nm due to an overtone of the Si:N-H vibration located around 3300 cm^{-1} ($k=1/(n\lambda)$, where n is the order of the overtone, here $n=2$). Even though the N-H vibration is at 1508 nm the "tail" of this peak extends into the telecom band giving rise to absorption at 1550 nm which is in the middle of the
10 telecom C-band (1530-1565 nm). Increasing the bandwidth to include the S- (1460-1530 nm) and the E- (1360-1460 nm) and the O-band (1260-1360 nm) the Si:N-H vibrations will be even more destroying when the aim is to fabricate low loss, high index contrast devices working over a broad wavelength range.

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The intensity of the Si:N-H absorption peak can be lowered by annealing the as deposited SiO_xN_y film to elevated temperatures (cf. e.g. "Silicon Oxynitride Layers for Optical Waveguide Applications", R. Germann et al., J. of Electrochemical Society, 147(6), p. 2237-2241 (2000) or "Passband
20 flattened binary-tree structured add-drop multiplexers using SiON waveguide technology", Ph. D Thesis by Chris Roeloffzen, Twente, 2002 (ISBN 90-365-1803-2)). Annealing temperatures as high as 1150 °C have been reported in the literature giving losses at the peak maxima of around 0.6 dB/cm. Unfortunately, it is not possible to completely remove the absorption peak by
25 simple annealing, and furthermore, the annealing approach also has another drawback of increasing the stress in the film layer giving rise to a significant increase in the birefringence of the film (the degree of birefringence being defined by the difference between the refractive indices n_{TE} and n_{TM} of the transverse electric (TE) and transverse magnetic (TM) modes, respectively).
30 This is clearly an unwanted side effect of extensive annealing.

A decrease in hydrogen-bond related loss upon annealing of SiON-type material is also discussed in US patent applications US-2002-0182342, US-2002-0194876 and US-2002-0178760, among others.

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The variety of different CVD processes discussed in the literature can be grouped into two different categories, i.e. a type A process using NH_3 as one of the gasses from which the film layer is formed and a type B process where the films are nucleated from a gas composition which is not containing NH_3 .

5 We have mapped out various different PECVD combinations of type A and B processes. In accord with the findings in the literature, we find that there is a fairly high loss around 1508 nm due to the presence of Si:N-H bonds in films based on both types of processes (cf. FIG. 4). This is also the case after annealing up to 16 hours at 1150 °C. However, the loss due to vibrating N-H

10 bonds is slightly lower for films formed on the basis of a type B recipe as compared to films formed by a type A recipe. Intuitively this is also expected, since a film based on a type A recipe is expected to contain a higher density of N-H bonds since N-H bonds are directly introduced into the film layer through fragments of the NH_3 molecule, e.g. NH_x , $x=1, 2$. In accord with the

15 literature we also saw that the absorption loss could be decreased by increasing the annealing temperature and/or the annealing time.

Unfortunately the improved losses obtained by annealing are still not low enough for low loss broad banded telecom related components.

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One way to reduce the hydrogen concentration in silicon oxynitride material of the stoichiometric form $\text{Si}_a\text{O}_x\text{N}_y\text{A}_z\text{M}_v\text{H}_u$ is according to WO-99/44937 to incorporate penta- or hexa-valent elements (A) from Group 15, 16 of the periodic system and/or mono- or di-valent metals (M) from groups 1, 2, 11 or

25 12 interstitially in the glass matrix. This is expected to reduce the hydrogen affinity of the nitrogen atoms and therefore to reduce the optical losses due to N-H-absorption. Preferred embodiments are elements of the stoichiometric form $\text{Si}_a\text{O}_x\text{N}_y\text{A}_z\text{M}_v\text{H}_u$ wherein $z \geq y$ and/or $v \geq y$, i.e. the concentration of Nitrogen is less than or equal to the concentration of A- (e.g. P, As, etc.) or M-elements (e.g. Li, Be, Cu, Zn. etc.).

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In EP-1295963 A2, EP-1273677 A2, and EP-1302792 A2 the optimization of process parameters such as flow rates, pressures, temperatures, gases, etc. in various steps of a PECVD process for deposition of silica films on a wafer

35 and subsequent heat treatment are described, the optimization being

performed with a view to reduce the optical absorption due to Si:N-H and Si:O-H oscillators.

5 No characterisation of propagation loss measurements on a finished planar waveguide has been performed in WO-99/44937. In EP-1295963 and EP-1273677 it is suggested to optimise the thermal treatment which allows the optical properties to be maintained while modifying the mechanical stress of the core. There is, however, no clear evidence for a correlation between optical loss and mechanical stress of the core layer, since the stress effect of
10 the upper cladding layer is not considered in the spectroscopy characterisation of the core layer.

DISCLOSURE OF INVENTION

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The object of the present invention is to provide an optical waveguide with low optical loss due to a reduced hydrogen bond-originated absorption. It is a further object to provide an optical waveguide with low optical loss due to absorption in a wavelength range used for optical transmission. In an
20 embodiment of the invention, it is a further object to lower or remove absorption peaks due to hydrogen bonds in an optical waveguide. In an embodiment of the invention, it is a further object to lower or remove absorption peaks due to N-H bonds in an optical waveguide. In an embodiment of the invention, it is a further object to lower or remove
25 absorption peaks due to O-H bonds in an optical waveguide. In an embodiment of the invention, it is a further object to lower or remove absorption peaks due to Si-H bonds in an optical waveguide.

The objects of the invention are achieved by the invention described in the
30 accompanying claims and as described in the following.

An optical waveguide for guiding light in a predefined wavelength range, the optical waveguide comprising core and cladding regions for confining light, the core and/or cladding region or regions being formed on a substrate, and
35 the whole or a part of the core and/or cladding region or regions comprising material of the stoichiometric composition $\text{Si}_a\text{O}_x\text{N}_y\text{X}_z\text{H}_v$, is provided by the

invention wherein X is selected from the group of elements B, Al, P, S, As, Sb and combinations thereof, and the ratio y/z is larger than 1, such as larger than 1.2, such as larger than 1.5, such as larger than 1.8, such as larger than 2.0, such as larger than 2.5, such as larger than 3.0, such as
5 larger than 3.5, such as larger than 4.0, such as larger than 4.5, such as larger than 5.0, such as larger than 5.5, such as larger than 6.0, such as larger than 7.0, such as larger than 8.0.

An advantage of the invention is that a low optical absorption in the
10 waveguide may be achieved. In an embodiment of the invention, a low absorption in the waveguide may be obtained over a broad wavelength range, e.g. in the range 1530-1565 nm. Further, in an embodiment of the invention, a relatively low annealing temperature may additionally be used yielding a relatively low induced strain whereby a low birefringence may be
15 achieved.

The present invention demonstrates that is possible to make an optical waveguide with low optical absorption properties in the S-, C-, L- and O-bands. In particular, it is possible to lower the density of Si:N-H bonds to
20 provide an absorption below 0.1 dB/cm (such as below 0.05 dB/cm) in a $\text{Si}_a\text{O}_x\text{N}_y\text{X}_z\text{H}_v$ type material where $y > z$, i.e. the concentration of X (e.g. P) is less than the concentration of N.

In an embodiment of the invention, it is further possible to tune the inherent
25 stresses by adjusting the y/z ratio or by adding a third element or a combination of elements. In an embodiment the amount of Phosphorus is used to optimize (e.g. to minimize) the inherent stresses of the optical waveguide.

30 In the present context, the term "waveguide" is taken to mean any elongate guide structure which permits the propagation of a wave throughout its length despite diffractive effects, and possibly curvature of the guide structure. "An optical waveguide" based on *total internal reflection* is defined by an extended region of increased index of refraction relative to the surrounding
35 medium. "An optical waveguide" based on a *photonic band gap* is defined by an extended core region surrounded by a photonic band gap material

comprising a periodic pattern of holes or a periodic pattern of high index material. The strength of the guiding, or the confinement, of the wave depends on the wavelength, the index difference and the guide width. Stronger confinement leads generally to narrower modes. An optical

5 waveguide may support multiple optical modes or only a single mode, depending on the strength of the confinement. In general, an optical mode is distinguished by its electromagnetic field geometry in two dimensions, by its polarization state, and by its wavelength. The polarization state of a wave guided in a birefringent material or an asymmetric waveguide is typically

10 linearly polarized. However, the general polarization state may contain a component of nonparallel polarization as well as elliptical and unpolarized components, particularly if the wave has a large bandwidth. If the index of refraction difference is small enough (e.g. $\Delta n = n_1 - n_2 = 0.036$) and the dimension of the guide is narrow enough (e.g. width $W = 3 \mu\text{m}$), the

15 waveguide will only confine a single transverse mode (the lowest order mode) over a range of wavelengths. If the waveguide is implemented on the surface of a substrate so that there is an asymmetry in the index of refraction above and below the waveguide, there is a cutoff value in index difference or waveguide width below which no mode is confined. A waveguide may be

20 implemented in a substrate (e.g. by diffusion into the substrate), on a substrate (e.g. by applying a coating and etching away the surrounding regions, or by applying a coating and etching away all but a strip to define the waveguide), inside a substrate (e.g. by contacting or bonding several processed substrate layers together). The optical mode which propagates in

25 the waveguide has a transverse dimension which is related to all of the confinement parameters, not just the waveguide width.

The width and height of a waveguide element is in the present context taken in a transversal cross section of the waveguide core (i.e. in a cross section

30 perpendicular to the intended direction of light guidance of said waveguide core elements at the location of a width measurement), the *width* being a dimension of the core region of the waveguide element in question in a direction *parallel* to a reference plane defined by the opposing, substantially planar, surfaces of the substrate (x-direction in FIG. 6), the *height* being a

35 dimension of the core region of the waveguide element in question in a

direction *perpendicular* to the reference plane (in a direction of growth, y-direction in FIG. 6).

The term "the stoichiometric composition" of a material" reflects the relative
 5 number of units of the elements in question present in the material, e.g. $\text{Si}_{0.97}\text{O}_{1.91}\text{N}_{0.09}\text{P}_{0.03}$ defining a material wherein (on average over a given volume of the material) for each 97 silicon atoms, 191 oxygen atoms, 9 nitrogen atoms and 3 phosphorus atoms are present. The suffixes or numbers a, x, y, z, v in the stoichiometric composition $\text{Si}_a\text{O}_x\text{N}_y\text{X}_z\text{H}_v$ represent
 10 the molar concentrations of the constituent elements calculated relative to the sum $a+x+y+z+v$, e.g. the relative concentration $c(\text{N})$ of the element nitrogen in the composition $\text{Si}_a\text{O}_x\text{N}_y\text{X}_z\text{H}_v$ equals $y/(a+x+y+z+v)$. In the present context, the atomic concentration of an element Q (e.g. H) measured in atomic% (at.%) is taken to mean $c(\text{Q}) \cdot 100$ (i.e. for hydrogen $c(\text{H}) \cdot 100 =$
 15 $v \cdot 100 / (a+x+y+z+v)$ in a $\text{Si}_a\text{O}_x\text{N}_y\text{X}_z\text{H}_v$ material).

The volume – termed a 'given volume' above - over which the composition is averaged - is preferably the total volume of the sample or layer having a given intended stoichiometric composition, e.g. the volume of the core.
 20 Alternatively, the 'given volume' may be a representative part of the total volume, i.e. a macroscopic part of the sample, such as more than 1% of the total volume of the part or layer in question, i.e. statistically large enough to allow a meaningful average value. Alternatively, the 'given volume' may be a volume that is at least 5 times the volume expected to comprise one unit of
 25 the stoichiometric composition in question, such as at least 100 times, such as at least 1000 times. Alternatively, the 'given volume' may be defined by a dimension comparable to the wavelength λ of the propagating wave in question, such as 2 times λ , such as 10 times λ .

30 The atomic density (atoms/unit volume, e.g. atoms/cm³) of the different elements in a given sample may e.g. be determined by Secondary Ion Mass Spectrometry (SIMS) measurement or by an energy-dispersive X-ray analysis (EDX) measurement. The basic principles of both techniques are discussed extensively in various textbooks, see e.g. "Fundamentals of
 35 surface and thin films analysis", L. C. Feldman, J. W. Mayer, ISBN 0-444-00989-2, wherein - for example - quantitative analysis down to an accuracy

of about 1 % by EDX is discussed. EDX is characterized by being a surface sensitive tool with electron penetration depths between 5 and 100 Å, depending on the energy of the incoming electron.

- 5 A connection between atomic concentration and relative molar concentration may be estimated by assuming or measuring a certain mass density $\rho(\text{SiONXH})$ of the resulting material (H may optionally be neglected due to its small contribution to the mass density). The atomic density N_{at} for a given element Q (Q = Si, O, N, X, H) is given by the formula

$$10 \quad N_{\text{at}}(\text{Q}) = c(\text{Q}) \cdot \rho(\text{SiONXH}) \cdot N_{\text{a}} / M_{\text{tot}}$$

- where $c(\text{Q})$, as mentioned above, is the relative concentration of the element Q in the composition $\text{Si}_a\text{O}_x\text{N}_y\text{X}_z\text{H}_v$, N_{a} is Avogadro's number (the number of atoms or molecules in a mole) and $M_{\text{tot}} = a \cdot M_{\text{Si}} + x \cdot M_{\text{O}} + y \cdot M_{\text{N}} + z \cdot M_{\text{X}} + v \cdot M_{\text{H}}$ is the mole mass (unit mass/mole, e.g. g/mole) of the $\text{Si}_a\text{O}_x\text{N}_y\text{X}_z\text{H}_v$ -material, where
- 15 M_{Q} is the atomic mass of element Q (e.g. $M_{\text{Si}} = 28.086$ g/mole).

- In an embodiment, the material further comprises Ge. In other words, Ge may be present in *combination* with one or more of the elements X= B, Al, P, S, As, Sb. This has the additional advantage of providing the possibility to
- 20 fine tune the refractive index and to tailor the photosensitivity of the material.

- In an embodiment of the invention, the optical waveguide comprises a cladding region surrounding the core region. In an embodiment of the invention, the cladding and the core region comprises material of the
- 25 stoichiometric composition $\text{Si}_a\text{O}_x\text{N}_y\text{X}_z\text{H}_v$ and wherein X is selected from the group of elements B, Al, P, S, As, Sb and combinations thereof (and/or in combination with Ge), and the ratio y/z is larger than 1. The index difference between core and cladding may e.g. be provided by changing the y/x ratio (i.e. changing the $[\text{N}]/[\text{O}]$ -concentrations, e.g. by changing the y/x ratio of the
- 30 feed gas in a CVD-process). In an embodiment of the invention, the core and/or cladding region or regions are constituted essentially of material of the stoichiometric composition $\text{Si}_a\text{O}_x\text{N}_y\text{X}_z\text{H}_v$. The term 'constituted essentially of material ...' is taken to refer to the elements of significance to the merits of the invention.

In an embodiment of the invention the, core region comprises material of the stoichiometric composition $\text{Si}_a\text{O}_x\text{N}_y\text{X}_z\text{H}_v$ and wherein X is selected from the group of elements B, Al, P, S, As, Sb and combinations thereof (and/or in combination with Ge). In this embodiment, the cladding region or regions
5 may comprise any type of material having an appropriate refractive index, e.g. a PBSG type glass or a PBG region.

In an embodiment of the invention the, waveguide comprises a core region and two or more surrounding cladding regions (e.g. two 'concentric' cladding
10 regions wherein at least one of the cladding regions comprises material of the stoichiometric composition $\text{Si}_a\text{O}_x\text{N}_y\text{X}_z\text{H}_v$ and wherein X is selected from the group of elements B, Al, P, S, As, Sb and combinations thereof (and/or in combination with Ge). In this embodiment, the core region may comprise any type of material having an appropriate refractive index, e.g. a PBSG type
15 glass or a PBG type glass or a Ge doped silica glass. In this embodiment, a further cladding region or regions may comprise any type of material having an appropriate refractive index, e.g. a PBSG type glass or a PBG region or SiO_2 .

20 In an embodiment of the invention, the ratio y/z is in the range 1.0 to 100, such as 1.0 to 20, such as 1.0 to 10, such as 1.5 to 8.0, such as 2.0 to 4.0, such as 2.5 to 3.5.

In an embodiment of the invention, the ratio y/z is essentially equal to 3.

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In an embodiment of the invention, the ratio y/z is essentially equal to 7.

The term 'essentially equal to' is in the present context taken to mean being within 10% of the value in question, such as within 5%, such as within 1%.

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In an embodiment of the invention, the number 'a' defining the relative concentration of the element Si is in the range 0.1 to 3.5, such as in the range 0.5 to 3.5 such as in the range 0.9 to 1.1 (e.g. SiO_2 -like) or in the range 2.9 to 3.1 (e.g. Si_3N_4 -like).

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In an embodiment of the invention, the number 'x' defining the relative concentration of the element O is in the range 0 to 2.5, such as in the range 1.9 to 2.1 (e.g. SiO₂-like) or in the range 0 to 0.1 (e.g. Si₃N₄-like).

- 5 In an embodiment of the invention, the number 'y' defining the relative concentration of the element N is in the range 0 to 4.5, such as in the range 3.9 to 4.1 (e.g. Si₃N₄-like) or in the range 0 to 0.5, such as in the range 0.02 to 0.3, such as in the range 0.03 to 0.2, such as in the range 0.04 to 0.10.
- 10 In an embodiment of the invention, the number 'z' defining the relative concentration of the element X selected from the group comprising B, Al, P, S, As, Sb and combinations thereof is in the range 0 to 0.3, such as in the range 0 to 0.2, such as in the range 0.005 to 0.2, such as in the range 0.01 to 0.10.
- 15 In an embodiment of the invention, the number 'v' defining the relative concentration of the element H is defined by $0 \leq v < 0.05$.
- 20 In an embodiment of the invention, 'a' is in the range 0.8 to 1.2 and 'x' is in the range 1.8 to 2.2 and 'y' is in the range 0.01 to 0.5 and 'z' is in the range 0.005 to 0.2. This illustrates the situation of a SiO₂-based SiONX-composition with comparatively small relative amounts of N and X-elements.
- 25 In an embodiment of the invention, 'a' is in the range 2.8 to 3.2 and 'x' is in the range 0.01 to 0.5 and 'y' is in the range 3.8 to 4.2 and 'z' is in the range 0.005 to 0.2. This illustrates the situation of a Si₃N₄-based SiONX-composition with minor relative portions of O and X-elements.
- 30 In an embodiment of the invention, the number 'a' defining the relative concentration of the element Si is in the range 0.9 to 1.1, the number 'x' defining the relative concentration of the element O is in the range 1.9 to 2.1, the number 'y' defining the relative concentration of the element N is in the range 0.015 to 0.12, and the number 'z' defining the relative concentration of the element X is in the range 0.005 to 0.04.

In an embodiment of the invention, the waveguide core and/or cladding layers comprise material of the stoichiometric composition $\text{Si}_{(1-z)}\text{O}_{(2-y)}\text{N}_y\text{X}_z$ wherein X is an element from the group comprising B, Al, P, S, As, Sb or a combination thereof.

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In an embodiment of the invention, the waveguide core and/or cladding layers consists essentially of material of the stoichiometric composition $\text{Si}_{(1-z)}\text{O}_{(2-y)}\text{N}_y\text{X}_z$ wherein X is an element from the group comprising B, Al, P, S, As, Sb or a combination thereof.

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In an embodiment of the invention, the waveguide core and/or cladding layers comprise material of the stoichiometric composition $\text{Si}_{(1-z)}\text{O}_{(2-y)}\text{N}_y\text{P}_z$. In an embodiment of the invention, $0 < y \leq 0.2$ and $0 < z \leq 0.1$. In embodiments of the invention, the atomic density of silicon $N_{\text{at}}(\text{Si})$ in the range $4.5 \cdot 10^{21} < N_{\text{at}}(\text{Si}) < 1.3 \cdot 10^{22}$, such as in the range $5.1 \cdot 10^{21} < N_{\text{at}}(\text{Si}) < 9.1 \cdot 10^{21}$, the atomic density of oxygen $N_{\text{at}}(\text{O})$ is in the range $9.0 \cdot 10^{21} < N_{\text{at}}(\text{O}) < 2.7 \cdot 10^{22}$, such as in the range $1.0 \cdot 10^{22} < N_{\text{at}}(\text{O}) < 1.8 \cdot 10^{22}$, the atomic density of nitrogen $N_{\text{at}}(\text{N})$ is in the range $0 < N_{\text{at}}(\text{N}) < 2.7 \cdot 10^{21}$, such as in the range $0 < N_{\text{at}}(\text{N}) < 1.8 \cdot 10^{21}$, and the atomic density of phosphorus $N_{\text{at}}(\text{P})$ is in the range $0 < N_{\text{at}}(\text{P}) < 1.3 \cdot 10^{21}$, such as in the range $0 < N_{\text{at}}(\text{P}) < 9.0 \cdot 10^{20}$.

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In an embodiment of the invention, the atomic density of at least one of the elements Si, O, N, P in $\text{Si}_{(1-z)}\text{O}_{(2-y)}\text{N}_y\text{P}_z$ is determined by SIMS.

25 In an embodiment of the invention, the atomic density of at least one of the elements Si, O, N, P in $\text{Si}_{(1-z)}\text{O}_{(2-y)}\text{N}_y\text{P}_z$ is determined by EDX.

In an embodiment of the invention, X comprises more than one element, such as two or more, such as m in total, each having a relative concentration compared to the total concentration z of X termed z_1 for X(1) and z_2 for X(2), etc., and z_m for X(m). The term "the element or elements X of the material $\text{Si}_a\text{O}_x\text{N}_y\text{X}_z\text{H}_v$ comprises at least $q_1\%$ of the element X(1)" is in the present context taken to mean that $q_1/100 = z_1/z$, where $z = \text{SUM}(z_i)$, $i=1, 2, \dots, m$, where $\text{SUM}(z_i)$ denotes the algebraic sum of the elements z_i . The relative concentration of the element X(i) in the material $\text{Si}_a\text{O}_x\text{N}_y\text{X}_z\text{H}_v$, on the other hand, is $z_i/(a+x+y+z+v)$.

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In an embodiment of the invention, the element or elements X or the material $\text{Si}_a\text{O}_x\text{N}_y\text{X}_z\text{H}_v$ comprises at least 50% phosphorus such as at least 75% phosphorus such as at least 90% phosphorus, such as 100% phosphorus.

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In an embodiment of the invention, the element or elements X or the material $\text{Si}_a\text{O}_x\text{N}_y\text{X}_z\text{H}_v$ comprises at least two elements X(1), X(2), ..., X(n) where $n \leq 7$, selected from the group comprising B, Al, P, S, Ge, As, Sb of relative concentrations z_1, z_2, \dots, z_n , respectively, where $z = z_1 + z_2 + z_3 + \dots + z_n$ and
10 wherein z_1/z is larger than 0.50 such as larger than 0.75 such as larger than 0.90.

In general, the addition of P, Ge and N to silica glass base increases the refractive index, whereas the addition of B decreases the refractive index of
15 the resulting waveguide material. In general, the addition of B and P increases the flow properties of a resulting silica glass. Interestingly, we have in connection with the present invention observed that the addition of P to SiON lowers the refractive index, suggesting that P might substitute N.

20 Recently it has been suggested (US2003/0021578) that the addition of Ge to a BPSG material allows for a decrease in P while retaining the same refractive index. As a consequence of the lower P-concentration, a smaller density of BPO_4 is formed during subsequent annealing, allowing for an improved reflow mechanism enabling the fabrication of high-aspect ratio
25 structures without keyhole formation (i.e. without voids or inclusions in the cladding material). Similarly, an improved reflow mechanism enabling the fabrication of high-aspect ratio structures without keyhole formation might be expected for $\text{Si}_a\text{O}_x\text{N}_y\text{X}_z\text{H}_v$ with X(1) = P, X(2) = Ge and X(3) = B.

30 In an embodiment of the invention, $n=2$ and X(1) is P and X(2) is B. In an embodiment of the invention, $n=2$ and X(1) is P and X(2) is Ge. This has the advantage that the relative concentrations of P and B or Ge may be used to fine tune the resulting refractive index.

In an embodiment of the invention, $n=3$ and $X(1)$ is P, $X(2)$ is B and $X(3)$ is Ge. This has the advantage that the relative concentrations of P, B and Ge may be used to fine tune the resulting refractive index.

- 5 In an embodiment of the invention, the optical absorption peak at $\lambda=1508$ nm due to Si:N-H bonds is smaller than 0.1 dB/cm, such as smaller than 0.05 dB/cm, such as smaller than 0.01 dB/cm, as measured e.g. by a planar version of a conventional cut-back-method.
- 10 The concentration of H is preferably so small that the optical absorption peak due to Si:N-H bonds is smaller than 0.1 dB/cm at $\lambda=1508$ nm, such as smaller than 0.05 dB/cm, such as smaller than 0.01 dB/cm. In an embodiment of the invention, the concentration of H is smaller than 10000 ppm (i.e. $v/(a+x+y+z+v) < 10^{-2}$), such as smaller than 1000 ppm, such as
- 15 smaller than 100 ppm, such as smaller than 10 ppm. In an embodiment of the invention, the relative concentration of H is much smaller than the relative concentration of N, i.e. e.g. $v < 10^{-2}y$, such as $v < 10^{-3}y$, such as $v < 10^{-4}y$. In an embodiment of the invention, the relative concentration of H is much smaller than the relative concentration of X, i.e. e.g. $v < 10^{-2}z$, such as
- 20 $v < 10^{-3}z$, such as $v < 10^{-4}z$, where X is an element selected from the group comprising B, Al, P, S, As, Sb and combinations thereof. In an embodiment of the invention, the atomic concentration of hydrogen is less than 25 at.%, such as less than 15 at.%, such as less than 5 at.%.
- 25 In an embodiment of the invention, the concentration of H is larger than the concentration of N or X or the concentration of N plus X (i.e. $v > y$, or $v > z$ or $v > y+z$). However, in this case a part of the hydrogen atoms may not contribute to the optical absorption around 1508 nm and/or may not be bound in the material in an N-H type bond. In an embodiment of the
- 30 invention, the concentration of hydrogen atoms in the material $Si_aO_xN_yX_zH_v$ is in the range 5 to 25 at.%, such as in the range 10 at.% to 20 at.%.

The hydrogen concentration of a sample may e.g. be determined by hydrogen nuclear reaction analysis (cf. e.g. "Fundamentals of surface and thin films analysis", L. C. Feldman, J. W. Mayer, ISBN 0-444-00989-2).

It should be noted that a small percentage of nitrogen impurity will mostly be present in CVD deposited glass when nitrogen is used as carrier gas or for example as part of the oxygen containing reaction gasses (i.e. N_2O or NH_3). The percentages of the nitrogen impurity in such deposited glasses may be low and are often not measured or reported, partly because of the difficulty of ascertaining the nitrogen content with a reasonable accuracy. The analytical detection problem represents one reason why the unusual properties and advantages of chemically bound nitrogen in glasses are neither fully understood nor appreciated in the industry.

In an embodiment of the invention, the core and/or cladding region comprises material having a refractive index in the range 1.45 – 2.02, such as in the range 1.45 to 1.60, such as in the range 1.48 to 1.56 at a wavelength of 1550 nm. This may e.g. be achieved by addition of minor amounts of dopant ions such as Ge or Al. This has the advantage of allowing the manufacture of a relatively high index-waveguide while avoiding the N-H-absorption peak.

The term "the refractive index" of a region or volume represented by a particular cross sectional area of the waveguide is in the present context taken to mean the geometrical refractive index. If the region in question is constituted by one homogeneous material with a specific refractive index, the geometric refractive index is the normal refractive index for a homogeneous material. If the region in question is constituted by several smaller areas each of a homogeneous material, the geometric refractive index is the geometrically weighted average of the normal refractive indices of these smaller areas, i.e. the sum of the products of refractive index n_i and ratio A_i/A of the partial area A_i in question to the area A of the whole region being considered (i.e. $\sum(n_i \cdot (A_i/A))$, $i=1, 2, \dots, m$, where m is the number of smaller (or partial) areas constituting the region being considered).

In some cases the effective refractive index n_{eff} is conveniently used to characterize properties of an optical waveguide. Instead of considering the true waveguide structure with core and cladding the light propagation may be described as a plane wave propagating in a homogeneous medium having a refractive index n_{eff} , the so-called effective refractive index. This effective

index is rooted in eigenvalue equations originating from Maxwell's equations. The effective refractive index of a bound mode is greater than the cladding refractive index, and lower than the core refractive index. The effective index is furthermore a function of the waveguide core cross-sectional geometry,
5 see e.g. H. Nishihara et al., "Optical Integrated Circuits", McGraw-Hill (1989).

An optical waveguide according to the invention may be used for guiding light of any wavelength. In an embodiment of the invention, the optical waveguide is adapted to guide light in a wavelength range located in the
10 range of 250 nm to 3.6 μm , such as in the range of 850 nm to 1800 nm. In an embodiment of the invention, the optical waveguide is adapted to guide light comprising wavelengths in the range of 1260 nm to 1660 nm, such as in the range 1530-1565 nm, or in the range 1460-1530 nm, or in the range 1360-1460 nm, or in the range 1260-1360 nm.

15 In an embodiment of the invention, the waveguide core and/or cladding further comprises one or more of the rare earth (RE) elements (i.e. the elements Ce, Pr, Nd, Pm, Sm, Eu, Gd, Tb, Dy, Ho, Er, Tm, Yb, Lu). In an embodiment of the invention, one or more of the RE elements are present in
20 concentrations in the range 50 to 5000 ppm (mole/mole) i.e. in a material of the stoichiometric composition $\text{Si}_a\text{O}_x\text{N}_y\text{X}_z\text{H}_v(\text{RE})_q$, $50 \cdot 10^{-6} < q/(a+x+y+z+v+q) < 5000 \cdot 10^{-6}$. This has the advantage of enabling the formation of an active waveguide (for an amplifier or laser type functionality) in combination with the
low absorption loss features.

25 In an embodiment of the invention, the core and/or cladding region or regions additionally comprise Ge in sufficient amounts to minimise internal stress due to thermal expansion or contraction of the waveguide. This has the advantage of enabling a reduce birefringence of the core and/or cladding
30 layers In an embodiment of the invention, the material(s) of the core and/or cladding region or regions comprise less than 5 at.% Ge.

In an embodiment of the invention, the thermal expansion of one or more of the layers constituting the core and cladding regions of the waveguide is/are
35 adapted to the thermal expansion of the substrate by adding one or more TE-dopant elements to said one or more layers of the waveguide. TE-

dopant' is used as an abbreviation for 'Thermal Expansion influencing dopants'.

5 In an embodiment of the invention, the TE-dopant element or elements is/are selected from the group of elements comprising Al, B, F, Ge, P, Ti, or combinations thereof.

10 In an embodiment of the invention, the TE-dopant element or elements are present in the core/and or cladding region or regions in molar concentrations in the range 0 to 5%, i.e. taken relative to the sum of the molar concentrations of Si, O, N, X, H, (and possibly RE-dopants) and TE-dopants.

15 In an embodiment of the invention, the TE-dopant element or elements are present in the core/and or cladding region or regions in amounts sufficient to provide a coefficient of thermal expansion between $1 \cdot 10^{-7} \text{ }^{\circ}\text{C}^{-1}$ and $15 \cdot 10^{-7} \text{ }^{\circ}\text{C}^{-1}$.

20 In an embodiment, the waveguide comprises Phosphorus in the core and/or in the cladding region(s).

25 In an embodiment, the optical waveguide comprises a buffer material constituting a barrier between the core and cladding regions and fully or partially surrounding the core region. In an embodiment, a barrier layer is only applied on top of the core region, thereby partially surrounding the core region. In an embodiment, a barrier layer is applied on top as well as below the core region, thereby fully surrounding the core region. An advantage of inserting the buffer layer or layers is that the tendency to formation of crystallites may be lowered or eliminated, whereby the out-diffusion of Phosphorus from the core region may be lowered or eliminated.

30 In an embodiment, the buffer material is selected from the group SiO_2 , Si_xN_y , (i.e. Si_xN_y may e.g. be Si_3N_4), PECVD BPSG with alternative B/P doping levels and combinations thereof.

35 In an embodiment of the invention, the optical waveguide takes the form of a planar waveguide formed on a substrate. In an embodiment of the invention,

the substrate is silicon. This has the advantage of facilitating large scale production. In an embodiment of the invention, the substrate is quartz. This has the advantage of inherently a lower cladding layer, and furthermore, induced stress from the substrate (e.g. silicon) is avoided.

5

In an embodiment of the invention, the waveguide is part of a photonic crystal structure, allowing the propagation of electromagnetic energy in a certain wavelength range to be controlled by the introduction of periodic structural features providing a photonic band gap (PBG).

10

In an embodiment of the invention, the optical waveguide is manufacture by chemical vapour deposition (CVD), such as plasma enhanced CVD (PECVD) or Atmospheric Pressure CVD (APCVD). This has the advantage of providing an industrially proven manufacturing technology which is reliable and readily scalable for large volumes.

15

Alternatively the waveguides may be manufactured by other techniques such as flame hydrolysis deposition or techniques for spinning materials on glass.

20 A method of manufacturing an optical waveguide for guiding light in a predefined wavelength range, the optical waveguide comprising core and cladding regions for confining light is furthermore provided by the present invention, the method comprising the steps of

A) providing a substrate,

25 B) forming a lower cladding layer on the substrate,

C) forming a core region of said optical waveguide on the lower cladding layer,

D) forming an upper cladding layer to cover the core region and the lower cladding layer;

30 wherein the whole or a part of said waveguide core and/or cladding region or regions comprise material of the stoichiometric composition $\text{Si}_a\text{O}_x\text{N}_y\text{X}_z\text{H}_v$ and X is selected from the group of elements B, Al, P, S, As, Sb and combinations thereof, and wherein $y > z$, such as larger than 1.2, such as larger than 1.5, such as larger than 1.8, such as larger than 2.0, such as
35 larger than 2.5, such as larger than 3.0, such as larger than 3.5, such as larger than 4.0, such as larger than 4.5, such as larger than 5.0, such as

larger than 5.5, such as larger than 6.0, such as larger than 7.0, such as larger than 8.0.

5 The method is easily integrated into proven state of the art manufacturing technologies of optical waveguides and integrated optical components having the advantages of corresponding (above mentioned) optical waveguides is provided.

10 In an embodiment of the invention, $0.5 < a < 3.5$, $0 < x < 2.5$, $0 < y < 4.5$, $0 < z < 0.2$.

In an embodiment of the invention, $0.5 < a < 3.5$, $0 < x < 2.5$, $0 < y < 4.5$, $0 < z < 0.2$ and $0 \leq v < 0.05$.

15 In an embodiment of the invention, $v \geq 0.05$. In an embodiment of the invention, v is larger than y or z or $y+z$. In an embodiment of the invention, the atomic concentration of hydrogen in the material $\text{Si}_a\text{O}_x\text{N}_y\text{X}_z\text{H}_v$ is less than 25 at.%, such as less than 15 at.%, such as less than 5 at.% or in the range 5 to 25 at.%, such as in the range 10 at.% to 20 at.%.

20 In an embodiment of the invention, $0.5 < a < 3.5$, $0 < x < 2.5$, $0 < y < 4.5$, $0 < z < 0.2$.

25 In an embodiment of the invention, $0.8 < a < 1.2$, $1.8 < x < 2.2$, $0.01 < y < 0.5$, $0.005 < z < 0.2$.

In an embodiment of the invention, $0.9 < a < 1.1$, $1.9 < x < 2.1$, $0.015 < y < 0.12$, $0.005 < z < 0.04$.

30 In an embodiment of the invention, $2.8 < a < 3.2$, $0.01 < x < 0.5$, $3.8 < y < 4.2$, $0.005 < z < 0.2$.

35 In an embodiment, the material further comprises Ge. In other words, Ge may be present in *combination* with one or more of the elements $X = \text{B}, \text{Al}, \text{P}, \text{S}, \text{As}, \text{Sb}$. This has the additional advantage of providing the possibility to fine tune the refractive index and to tailor the photosensitivity of the material.

In an embodiment of the invention, step C) comprises the sub-steps
C1) forming a core layer on the lower cladding layer,
C2) providing a core mask comprising a core region pattern corresponding to
5 the layout of the core region of said optical waveguide, and
C3) forming core regions using the core mask, a photolithographic and an
etching process. This has the advantage of availing the use of industry
standard manufacturing processes, well-known from the manufacture of
integrated semiconductor as well as optical circuits.

10

In an embodiment, a sub-step
C4) of forming a barrier layer on top of said core region pattern, and
optionally on top of the lower cladding layer not covered by the core region
pattern;
15 is inserted before step D). An advantage of inserting the buffer layer or
layers is that the tendency to formation of crystallites may be lowered or
eliminated, whereby the out-diffusion of Phosphorus from the core region
may be lowered or eliminated.

20 In an embodiment, a sub-step C0) of forming a barrier layer on top of said
lower cladding layer is inserted before step C1). This has the advantage of
facilitating the formation of a barrier layer surrounding core region of the
waveguide.

25 In an embodiment, a sub-step of annealing is inserted after said barrier
forming step or steps C0), C4). This has the advantage of allowing reflow of
the barrier layer before applying other layers, e.g. an upper cladding layer.

In an embodiment of the invention, the substrate is a silicon or quartz
30 substrate.

In an embodiment of the invention, the optical waveguide is manufacture by
chemical vapour deposition (CVD), such as plasma enhanced CVD (PECVD)
or Atmospheric Pressure CVD (APCVD). This has the advantage of
35 providing an industrially proven manufacturing technology which is reliable
and readily scalable for large volumes.

In an embodiment of the invention, a standard cluster tool CVD process chamber type PECVD-apparatus from Surface Technology Systems is used for the formation of layers on the substrate.

5

- In an embodiment of the invention,
the N₂ flow rate is in the range 0-2000 sccm,
the N₂O flow rate is in the range 100-400 sccm,
the NH₃ flow rate is in the range 0-300 sccm,
10 the SiH₄ flow rate is in the range 0-30 sccm,
the 5% PH₃ in N₂ flow rate is in the range 0-50 sccm,
the power is in the range between 0 and 1200 W,
the pressure is in the range 50-500 mTorr,
the temperature is in the range 200-400 °C,
15 the frequency is around 380 kHz or around 13.56 MHz,

The unit sccm is short for Standard Cubic Centimeters per Minute being defined as a cubic centimetre at standard pressure and temperature (i.e. atmospheric pressure and 0 °C).

20

In an embodiment, the X=P and in i) the PH₃ flow is provided by PH₃ diluted in N₂ or another carrier gas.

- In an embodiment, in i) the PH₃ flow is provided by 5% PH₃ in N₂ with a flow
25 rate of 0 to 50 sccm such as 2 to 20 sccm.

In an embodiment, X comprises P and in i) the PH₃ flow is provided by PH₃ diluted in N₂ or another carrier gas and the PH₃ flow value is used as a stress optimization parameter for the core region.

30

In an embodiment, processing parameters of the PECVD process essentially have the following values:

- a) SiH₄ flow rate 20 sccm;
- b) the N₂O flow rate 100-400 sccm;
- 35 c) the N₂ flow rate 2000 sccm;
- d) the NH₃ flow rate is 100 sccm;

- e) the power is 700 W;
- f) the pressure is 250 mTorr;
- g) the temperature 350 °C;
- h) the frequency is 380 kHz;
- 5 i) 5%PH₃ in N₂ flow rate 10 sccm.

In an embodiment, in step i) the flow gas is selected among the group of gases SiH₄, SiF₄, SiCl₄, SiF₄, Si₂H₆, SiH₂Cl₂, SiCl₂F₂, SiH₂F₂, N₂O, NO, N₂, NO₂, O₂, H₂O, H₂O₂, CO, CO₂, N₂O, NO, N₂, NO₂, NH₃, N₂, B₂H₆, AlH₃, PH₃,
10 H₂S, SO, SO₂, GeH₄, AsH₃, or combinations thereof.

An optical waveguide obtainable by a method of manufacturing as described above is moreover provided by the present invention. Such a waveguide has the same advantages as for the waveguides outlined above.

15

An optical device comprising an optical waveguide as defined above is further provided by the present invention. Examples of devices wherein waveguides according to the invention could be useful are e.g. splitters, couplers, e.g. an arrayed waveguide grating (AWG), a generalized Mach-Zehnder interferometer, and any other functional units being part of an optical communication system. In an embodiment, waveguides according to the invention are included in a duplexer or triplexer. An optical triplexer is an optical component allowing the combination of digital communication and analogue video reception via an optical waveguide. Such a component is
20 e.g. useful in fibre-to-the-home solutions.

In an embodiment, an optical triplexer (or more precisely expressed 'triplex transceiver component') gives full-duplex digital communication over a single fiber (1310 nm upstream laser emission and 1490 nm downstream detection)
30 with an additional analogue video receiver (at 1550 nm). The triplex transceiver may be established by hybrid mounting of active devices (laser and photo diodes) on a passive planar light chip established by use of the glass material of the present invention. In a preferred version the triplex transceiver is hybrid mounted by use of a single step solder process for
35 simple interface and support of high volume assembly.

The use of the inventive glass material is advantageous in combination with the triplex transceiver due to the absence of the 1508 nm NH-absorption peak while maintaining the ability to use high index contrast waveguides giving raise to reduced chip size.

5

It should be emphasized that the term "comprises/comprising" when used in this specification is taken to specify the presence of stated features, integers, steps or components but does not preclude the presence or addition of one or more other stated features, integers, steps, components or groups thereof.

10

BRIEF DESCRIPTION OF DRAWINGS

15 The invention will be explained more fully below in connection with a preferred embodiment and with reference to the drawings in which:

FIG. 1 shows the refractive index at $\lambda=1550$ nm for the core region of various optical waveguides according to the invention, before and after annealing, respectively,

20

FIG. 2 shows corresponding values of layer thickness (closed symbols) and refractive index (open symbols) at $\lambda=1550$ nm for the core region of a waveguide according to the invention as a function of annealing temperature,

25

FIG. 3 shows a measure for the birefringence at $\lambda=1550$ nm of a waveguide according to the invention as a function of annealing temperature,

FIG. 4 shows optical absorption loss in dB/cm from $\lambda=1500$ nm to $\lambda=1600$ nm for a waveguide manufactured according to different processing conditions, respectively, 'with NH_3 ', 'without NH_3 ' and a 'new process' according to the invention,

30

FIG. 5 shows optical propagation loss in dB at $\lambda=1550$ nm for a waveguide according to the invention as a function of waveguide length (in cm) and mode (TE or TM),

35

FIG. 6 shows a cross section of a part of an optical component according to the invention,

- 5 FIG. 7a shows an isolated waveguide *without* neighboring particle formation, and FIG. 7b shows neighboring waveguides *with* particle formation, and

FIG. 8 shows birefringence vs. refractive index at $\lambda=1550$ nm for optical waveguides according to the invention manufactured using different PH_3 flow
10 rates.

The figures are schematic and simplified for clarity, and they just show details which are essential to the understanding of the invention, while other
15 details are left out. Throughout, the same reference numerals are used for identical or corresponding parts.

MODE(S) FOR CARRYING OUT THE INVENTION

20

A process according to the invention may be optimized as regards providing a waveguide with a low optical absorption around $\lambda=1508$ nm using one or more of the hints listed below:

- 25 1. Avoid NH_3 since this is an additional hydrogen source and contains an NH-bond.
2. Lower the SiH_4 flow since this is also a potential hydrogen source.
3. Increase the plasma power since more Si-H bonds will be broken allowing for less incorporation of hydrogen containing Si fragments as
30 compared to when the plasma process is driven at a lower power where it is expected that a smaller amount of Si-H bonds are broken.
4. Increase the total flow since this will flush out the reaction products the most undesirable being hydrogen and hydrogen containing fragments.
5. Increase the temperature since this is expected to decrease the
35 concentration of hydrogen in the plasma grown PECVD glass.

6. Changing the pressure will change the fragmentation degree of the molecules in the plasma and hereby changing the properties of the grown film.
7. Changing the frequency of the energy source driving the plasma will alter the properties of the PECVD grown film.
8. Add a small amount of (optionally diluted) PH_3 .

A Combination of one or more of the above mentioned elements may result in a total removal of the N-H peak an overtone of which causes extensive absorption at 1508 nm when a PECVD grown core glass is used as an optical waveguide.

In various embodiments of the present invention, the waveguide materials comprise a number of the following elements Si, O, N, X ('X' = B, Al, P, S, As, Sb), H, RE-dopants ('RE' = Ce, Pr, Nd, Pm, Sm, Eu, Gd, Tb, Dy, Ho, Er, Tm, Yb, Lu), TE-dopants ('TE' = Al, F, Ge, Ti, B, P) in the stoichiometric composition $\text{Si}_a\text{O}_x\text{N}_y\text{X}_z\text{H}_v(\text{RE})_q(\text{TE})_p$, where X denotes one or more of the elements 'X' for controlling refractive index and/or optical absorption properties and/or thermal expansion properties, RE one or more of the rare-earth elements 'RE' for controlling optical gain, and TE one or more of the elements 'TE' for controlling thermal expansion.

PECVD also known as Plasma CVD (PCVD) and Low Pressure Chemical Vapour Deposition (LPCVD) are described in further detail in Hiroshi Nishihara, Masamitsu Haruna and Toshiaki Suhara "Optical integrated circuits", McGraw-Hill Book Company, (1989), and in Chapter 3 in Marc Madou: "Fundamentals of Microfabrication", ISBN 0-8493-9451-1, which are incorporated herein by reference.

EXAMPLE 1

A PECVD core glass has been grown on a standard PECVD apparatus (in this case a standard cluster tool CVD process chamber type PECVD-apparatus from STS (Surface Technology Systems plc of Newport, South Wales, UK) is used for the formation of layers on a silicon substrate using the following parameters:

- a) SiH_4 flow rate: 20 sccm
- b) N_2O flow rate: 100-400 sccm
- c) N_2 flow rate: 2000 sccm
- 5 d) 5% PH_3 in N_2 flow rate: 10 sccm
- e) Power: 700 W
- f) Pressure: 250 mTorr
- g) Temperature: 350 °C
- h) Frequency: 380 kHz

10

FIG. 1 shows the refractive index at $\lambda=1550$ nm for the core region of various optical waveguides according to the invention, before and after annealing, respectively. Annealing was performed at 1100 °C for 4 hours in a nitrogen atmosphere.

15

The refractive index may easily be tuned in a fairly large range and significantly larger than indicated in FIG. 1. The refractive index change is completely governed by the ratio of nitrogen to oxygen atoms in the PECVD feed gas (at constant SiH_4 flow) as indicated by the linear relation of the refractive index as a function of the $[\text{N}]/[\text{O}]$ ratio (cf. FIG. 1). Here $[\text{N}] = 2 \cdot [\text{N}_2\text{O}] + 2 \cdot [\text{N}_2] + 0.95 \cdot [5\% \text{PH}_3/\text{N}_2]$ and $[\text{O}] = [\text{N}_2\text{O}]$ where $[\text{xx}]$ denotes the flow rate of species xx in sccm.

FIG. 2 shows corresponding values of layer thickness and refractive index at $\lambda=1550$ nm for the core region of a waveguide according to the invention as a function of annealing temperature. Open symbols indicate refractive index at $\lambda=1550$ nm. Closed symbols indicate layer thickness in μm . Atomic densities of nitrogen and phosphorus are $[\text{N}] = 1.30 \cdot 10^{21}$ atoms/ cm^3 and $[\text{P}] = 4.58 \cdot 10^{20}$ atoms/ cm^3 , respectively, as determined by calibrated SIMS.

30

The index of the as deposited PECVD glass can be modified upon annealing as seen in FIG. 2. The index change is initiated above approximately 800 °C and continues beyond 1100 °C.

35 FIG. 3 shows a measure for the birefringence at $\lambda=1550$ nm of a waveguide according to the invention as a function of annealing temperature.

The index change is correlated with an increase in the birefringence as seen from FIG. 3 where the difference between refractive index for TE and TM modes measured at $\lambda=1550$ nm is plotted as a function of the temperature.

- 5 Thus, it is suggested to use a relatively low annealing temperature in order to minimize the build up of birefringence. However, the applied annealing temperature should of cause be compatible with subsequent cladding procedure.
- 10 An optical component including a waveguide according to the present invention may be manufactured by a method comprising the steps of
 - A) providing a substrate,
 - B) forming a lower cladding layer on the substrate,
 - C1) forming a core layer on the lower cladding layer,
 - 15 C2) providing a core mask comprising a core region pattern corresponding to the layout of the core regions of optical waveguide elements of the component,
 - C3) forming core regions using the core mask, a photolithographic and an etching process,
 - 20 D) forming an upper cladding layer to cover the core region pattern and the lower cladding layer, and
 - E) annealing in a controlled atmosphere.

The annealing step E) may e.g. be performed after the deposition of the core
25 layer and/or in connection with successive upper deposition and annealing steps.

- In an embodiment of the present invention a clean and bare Silicon wafer (used as substrate, step A) is firstly oxidized (step B) to provide an optical
30 isolation layer (the 'buffer layer') of silica sufficiently thick that the magnitude of the evanescent field tail of the field pertaining to the waveguide cores is sufficiently low to ensure negligible propagation loss. On top of the buffer layer a layer (termed the 'core layer') of $\text{Si}_a\text{O}_x\text{N}_y\text{X}_z\text{H}_v(\text{RE})_q(\text{TE})_p$ (with meaning as described above) is deposited (step C1), containing one or more
35 dopants that effectively act to control the refractive index of the layer, to make it optically active, and/or to adapt its thermal expansion properties to

those of the substrate. Depending upon the method used to deposit the core layer a high temperature treatment (known as an anneal step) may be advantageous in order to stabilize the optical and/or mechanical properties of the layer. The optical waveguide circuitry is defined through standard optical lithography where a UV-transparent plate containing typically a chromium pattern replica of the waveguide design pattern (step C2) is pressed against a layer of UV-sensitive polymer which has been spin coated onto the surface of the core layer, subsequently the UV-sensitive polymer is exposed through the mask and the pattern is developed (step C3). Following the exposure and development of the waveguide pattern into the polymer layer, the polymer pattern is used as masking material for dry etching (e.g. RIE – Reactive Ion Etching, ICP – Inductively Coupled Plasma) into the core layer (step C3). In step C2), alternatively, a second mask system can be sandwiched between the core layer and the UV-sensitive polymer layer, which is used to enhance selectivity and waveguide core profile. In an embodiment of the invention this second mask system may consist of oxide/polymer or nitride/polymer such as discussed for oxide polymers by J. M. Moran and D. Maydan: "High resolution, steep profile resist patterns" J. Vac. Sci. Technol., Vol. 16, No 6, Nov./Dec. 1979 and for nitride polymers by H. Namatsu, Y. Ozaki, and K. Hirata, "high resolution trilevel resist", J. Vac. Sci. Technol., 21(2), July/aug. 1982. In this way the design waveguide pattern is transferred into the core layer having predetermined cross-sectional properties as well as refractive index. In order to protect the thus defined waveguide core, and in order to enhance symmetry in the structure transverse to the direction of propagation, a layer of silica with optical properties as close to those of the buffer layer as the chosen fabrication technology permits is deposited on top of the core structure (step D). The formation of the latter layer (e.g. termed the upper cladding layer) may be formed using successive deposition and annealing steps (i.e. successive repetitions of steps D and E). It may be advantageous to ensure that the upper cladding layer has a lower flow temperature than that of the core and lower cladding layers. This may be controlled by proper addition of boron, phosphorus and/or fluorine (or any other dopants that reduces the flow temperature to the upper cladding layer).

A sample with a refractive index contrast of $\Delta n/\langle n \rangle = 2.5\%$ was made according to the above mentioned procedure on top of 12 micron thermal

oxide (SiO_2). Spiral waveguides with a cross section of $3 \times 3 \text{ micron}^2$ was fabricated and subsequently cladded with an optimized cladding procedure (a standard BPSG-cladding). The hereby obtained waveguides were characterized (as described in B. H. Larsen, et al., We1.2.6, ECOC-IOOC, 2003) by direct, and hence, reliable propagation losses after propagation through up to 1 meter of waveguides. These characterization experiments reveal that when applying the parameters listed in EXAMPLE 1, it is possible to remove the overtone of the N-H absorption peak located at 1508 nm as indicated by the curve 'new process' in FIG. 4 illustrating optical absorption loss in dB/cm from $\lambda=1500 \text{ nm}$ to $\lambda=1600 \text{ nm}$ for a waveguide manufactured according to different processing conditions, respectively, 'with NH_3 ', 'without NH_3 ' and a 'new process' according to the invention.

By measuring the propagation loss as a function of the length at 1550 nm we have managed to fabricate waveguides with an extremely low loss below 0.03 dB/cm over a very broad range of wavelengths, as seen in FIG. 5 showing optical propagation loss in dB at $\lambda=1550 \text{ nm}$ for a waveguide according to the invention as a function of waveguide length (in cm) and mode (TE or TM).

The sample made by the parameters listed under EXAMPLE 1 has been analyzed by Secondary Ion Mass Spectrometry (SIMS). Briefly the sample under investigation is sputtered by a flux of accelerated ions (here Cs^+) by which material is continuously being removed from the surface layer. A simple monitoring and on-line analysis of fragments produced by sputtering will allow for chemical analysis as a function of sputtering time. By calibration of sputtering yield and by comparison with relevant references, the intensity of relevant fragments can directly be converted into concentrations (here e.g. N and P are relevant).

For the sample made by the procedure described in EXAMPLE 1 the N and P concentrations were determined to $[\text{N}]=1.30 \cdot 10^{21} \text{ atoms/cm}^3$ and $[\text{P}]=4.58 \cdot 10^{20} \text{ atoms/cm}^3$ corresponding to an $[\text{N}]/[\text{P}]$ ratio of 2.83.

Assuming a density close to 2.3 g/cm^3 as has been reported for SiON-type materials (cf. "Plasma-enhanced growth, composition and refractive index of

silicon oxy-nitride films", K. E. Mattsson, J. Appl. Phys. 77, No. 12, p.6616-6623, 1995) and a molar weight close to that of SiO₂ (28.086 g/mole + 2•15.999 g/mole = 60.0840 g/mole) one can convert the measured atomic densities to stoichiometric values since the density of a SiON type material is
 5 close to 2.3 g/cm³ / 60.0840 g/mole = 0.0383 mole/cm³. Multiplying with Avogadro's constant N_a one obtain an atom density of 2.3052•10²² atoms/cm³.

This leads to the following relative concentrations y and z of nitrogen and
 10 phosphorus, respectively:

$$N_y: y = 1.30 \cdot 10^{21} / 2.3052 \cdot 10^{22} = 0.056$$

$$P_z: z = 4.58 \cdot 10^{20} / 2.3052 \cdot 10^{22} = 0.020$$

15 EXAMPLE 2

A sample comprising an optical waveguide according to the invention was made as described in example 1 with the only difference that the 5%PH₃/95%N₂ gas flow was increased from 10 to 50 sccm. The hereby
 20 grown PECVD films delaminated upon annealing due to the high P-content. Thus, there is an upper limited to the amount of PH₃ which can be present under PECVD growth of a core under the above mentioned process parameters.

25 EXAMPLE 3

A sample comprising an optical waveguide according to the invention was made as described in example 1. The structure of the resulting waveguides were subsequently analyzed by Scanning Electron Microscopy (SEM) of
 30 polished cross sectional cuts. FIG. 7a shows the resulting waveguide profiles for an isolated waveguide 100 comprising core 33, lower 61 and upper 62 cladding regions. From FIG. 7a, it is evident that the waveguide core 33 (having a width of app. 7 μm as indicated in the SEM-photo) is (partially) surrounded by the upper cladding layer 62, and furthermore, no defects can
 35 be seen close to the waveguide core region. For closer spaced waveguides (e.g. for edge-to-edge spacings 72 less than 4 μm, cf. FIG. 7b), one

observes an apparent reaction between the (upper) cladding layer 62 and the waveguide core material 33 resulting in the nucleation and growth of small crystallites/particles 71 next to the waveguide core regions. FIG. 7b shows a representative SEM image of this particle formation process in-
5 between neighboring waveguide core regions (here having an edge to edge spacing of 5 μm as indicated in the SEM-photo). It has surprisingly turned out that the formation of these crystallites can be prevented by adding a buffer layer between the core region and the upper cladding layer. In the present case a buffer layer of 0.35 μm undoped PECVD SiO_2 on top of the
10 etched core layer was enough to avoid crystallite/particle formation. The appropriate minimum thickness depends on the dopant levels of the core and cladding, respectively (higher dopant levels => higher thickness). The buffer layer thickness is preferably in the range from 0.2 μm to 1.0 μm . Other buffers/barriers such as PECVD BPSG with alternative B/P doping levels,
15 SiON , Si_xN_y (e.g. Si_3N_4), etc. (and correspondingly optimized layer thicknesses) might be applied.

In a preferred embodiment of the method outlined in Example 1, a sub-step "C4) of forming a barrier layer on top of said core region pattern, and
20 optionally on top of the lower cladding layer not covered by the core region pattern;"

is inserted before step D) of forming an upper cladding layer to cover the core region pattern and the lower cladding layer. Optionally, a barrier layer may be applied below the core region pattern by inserting a sub-step C0) of
25 forming a barrier layer on top of said lower cladding layer. The latter has the advantage of fully isolating the core layer from the lower and upper cladding layers. An optional annealing step may be inserted after the barrier layer formation step(s) to relax the barrier layer. An advantage of inserting the buffer layer or layers is that the tendency to formation of crystallites may be
30 lowered or eliminated. Thereby the out-diffusion of Phosphorus from the core region may be lowered or eliminated. It may further have the advantage of reducing stress in the waveguide core. These effects of the inclusion of a barrier layer between the core and cladding regions are particularly advantageous for waveguides according to the present invention for which
35 the concentration (y) of X (including e.g. P) is larger than the concentration (z) of N (i.e. for $y/z > 1$ as defined by the present invention).

It might be tempting to associate the observed particles due to the formation of B_2O_3 , P_2O_5 or BPO_4 , crystallites. Formation of such particles has been observed as a consequence of Boron and Phosphorus segregation during
5 annealing of BPSG films (see e.g. S. Imai et al., Appl. Phys. Lett. 60(22), p.1761). Thus, adding the above mentioned buffer will clearly alter the relative concentration of B and P preventing the local nucleation and growth of crystallites.

10 EXAMPLE 4

A core made according to Example 1 has been made with two different PH_3 flows. The index was in both cases tuned by adjusting the N_2O flow keeping everything else constant. From FIG. 8, it is evident that it is possible to bridge
15 an index range (measured at 1550 nm) from approximately 1.44 up to 1.5 for both series of PH_3 flows. From the figure it is interesting to note that the birefringence ($n(TE)-n(TM)$) is lowest for the 5 sccm PH_3 series 81 as compared to the 15 sccm PH_3 series 82. Furthermore, for the 15 sccm series it is observed that the birefringence increases with increasing
20 refractive index whereas it stays approximately constant for the 5 sccm PH_3 series at a lower value of $-2 \cdot 10^{-3}$ to $-3 \cdot 10^{-3}$.

Thus the exact PH_3 flow value can be used as an additional stress optimization parameter when tuning the exact core process in connection
25 with further applications of this type of core.

BASIC ELEMENTS

30 For waveguides according to the invention comprising material of the composition $Si_aO_xN_yX_zH_v$, the individual elements may be introduced – mainly from a vapour phase – from the following compounds:

35 **Silicon, Si:**

SiH₄, SiF₄, SiCl₄, SiF₄, Si₂H₆, SiH₂Cl₂, SiCl₂F₂, SiH₂F₂ or any other silicon containing gases or solids involving the use of hydrogen, chlorine, oxygen or even from solid compounds such as SiO_x or spin on type glasses as well as sol-gel compounds containing Si.

5

Oxygen, O:

N₂O, NO, N₂, NO₂, O₂, H₂O, H₂O₂, CO, CO₂

Nitrogen, N:

10 N₂O, NO, N₂, NO₂, NH₃, N₂

Boron, B:

B₂H₆ or from solid compounds such as B₂O₃

15 **Aluminum, Al:**

AlH₃ or liquid solved Organo-Al complexes

Phosphorus, P:

PH₃

20

Sulfur, S:

H₂S, SO, SO₂

Germanium, Ge:

25 GeH₄ or solid compounds such as GeO₂

Arsenic, As:

AsH₃

30 **Antimony, Sb:**

Sb dissolved in Organo compounds.

Carrier gas selected from:

N₂, He, Ne, Ar, Kr, Xe

35

AN EXAMPLE BASED ON ATOMIC CONCENTRATIONS

In the following a correlation is established between relative stoichiometric concentrations (the a, x, y, z, v's in $\text{Si}_a\text{O}_x\text{N}_y\text{X}_z\text{H}_v$) and corresponding atomic densities for various mass densities of the resulting material. This is e.g. of use when a SIMS measurement is made to determine the atomic concentration of a given sample.

The 'atomic' concentration (units $\text{Si}_a\text{O}_x\text{N}_y\text{X}_z\text{H}_v/\text{cm}^3$) in a given volume of a $\text{Si}_a\text{O}_x\text{N}_y\text{X}_z\text{H}_v$ type material is calculated as the mass density (ρ (g/cm^3)) divided by the mole mass M_{tot} (g/mole) multiplied by Avogadro's number N_a . The total mole mass of $\text{Si}_a\text{O}_x\text{N}_y\text{X}_z\text{H}_v$ is given by a weighted sum of the mole masses of the constituting elements, i.e. $M_{\text{tot}} = a \cdot M_{\text{Si}} + x \cdot M_{\text{O}} + y \cdot M_{\text{N}} + z \cdot M_{\text{X}} + v \cdot M_{\text{H}}$.

The individual atom densities N_{at} (atoms/cm^3) of each type of atom will then be given by:

$$\begin{aligned} N_{\text{at}}(\text{Si}) &= a/(a+x+y+z+v) \cdot \text{total number of atoms} = a \cdot \rho \cdot N_a / [(a+x+y+z+v) \cdot M_{\text{tot}}] \\ N_{\text{at}}(\text{O}) &= x/(a+x+y+z+v) \cdot \text{total number of atoms} = x \cdot \rho \cdot N_a / [(a+x+y+z+v) \cdot M_{\text{tot}}] \\ N_{\text{at}}(\text{N}) &= y/(a+x+y+z+v) \cdot \text{total number of atoms} = y \cdot \rho \cdot N_a / [(a+x+y+z+v) \cdot M_{\text{tot}}] \\ N_{\text{at}}(\text{X}) &= z/(a+x+y+z+v) \cdot \text{total number of atoms} = z \cdot \rho \cdot N_a / [(a+x+y+z+v) \cdot M_{\text{tot}}] \\ N_{\text{at}}(\text{H}) &= v/(a+x+y+z+v) \cdot \text{total number of atoms} = v \cdot \rho \cdot N_a / [(a+x+y+z+v) \cdot M_{\text{tot}}] \end{aligned}$$

In an embodiment of the invention the above method can be illustrated by assuming a type of structure such as $\text{Si}_{(1-z)}\text{O}_{(2-y)}\text{N}_y\text{P}_z$ wherein P is taken as an example from the group of elements denoted by X in the general formula ('X' = B, Al, P, S, As, Sb). In this example, P is assumed to substitute Si and N to substitute O. The addition of a small amount of H_v (either intentionally or unintentionally) is not expected to have a major impact on either ρ or M_{tot} due the small size and mass of hydrogen as well as the small concentration of H expected. However, the local presence of H might be important since the material should be valence neutral, i.e. $(1-z) \cdot [\text{oxidation state of Si}] + (2-y) \cdot [\text{oxidation state of O}] + y \cdot [\text{oxidation state of N}] + z \cdot [\text{oxidation state of P}] + v \cdot [\text{oxidation state of H}] = 0$.

The reported oxidation states are:

H:

+1 and -1 with +1 being the most obvious configuration in connection with covalent hydrides

5 O:

-2 and -1, with -2 being the most obvious state

Si:

+4, +6, -2, with +4 being the most stable configuration in connection with

10 SiO₂ like materials

N:

+3, -3, +4, +5, with the -3 state being the most stable configuration in the present content

15

P:

+3, +5, -3, with +5 being the most stable state.

Thus one can write:

20 $(1-z) \cdot (+4) + (2-y) \cdot (-2) + y \cdot (-3) + z \cdot (+5) + v \cdot (+1) = 4 - 4z - 4 + 2y - 3y + 5z + v = z - y + v = 0$,
i.e. $z = y - v$, assuming the above mentioned oxidation states of the individual compounds. Thus in this simple model, a small amount of hydrogen will allow for $z < y$, i.e. for more nitrogen than phosphors. Alternative valance states of the constituents may not be neglected.

25

Assuming a Si_(1-z)O_(2-y)N_yP_z type of material, z will be between 0 and 1 and y will be between 0 and 2. In an embodiment of the invention, z will be between e.g. 0 and 0.2 and y will be between 0 and 0.1 and $y > z$. The presence of hydrogen is not incorporated in the following calculations
30 although a small amount may be present.

In the above mentioned intervals, M_{tot} has been calculated as:

$M_{tot} = (1-z) \cdot M_{Si} + (2-y) \cdot M_O + y \cdot M_N + z \cdot M_P$, with

$M_{Si} = 28.086$ g/mole

35 $M_O = 15.999$ g/mole

$M_P = 30.974$ g/mole

$M_N = 14.007 \text{ g/mole}$

The result for M_{tot} has been summarized in table 1. As can be seen from table 1, M_{tot} is only varying between 59.69 g/mole and 60.17 g/mole.

5

mole mass (g/mole)		y																				
z		0	0.01	0.02	0.03	0.04	0.05	0.06	0.07	0.08	0.09	0.1	0.11	0.12	0.13	0.14	0.15	0.16	0.17	0.18	0.19	0.2
0		60.08	60.06	60.04	60.02	60.00	59.98	59.96	59.94	59.92	59.90	59.88	59.86	59.84	59.83	59.81	59.79	59.77	59.75	59.73	59.71	59.69
0.01			60.09	60.07	60.05	60.03	60.01	59.99	59.97	59.95	59.93	59.91	59.89	59.87	59.85	59.83	59.81	59.79	59.77	59.75	59.73	59.71
0.02				60.10	60.08	60.06	60.04	60.02	60.00	59.98	59.96	59.94	59.92	59.90	59.88	59.86	59.84	59.82	59.80	59.78	59.76	59.74
0.03					60.11	60.09	60.07	60.05	60.03	60.01	59.99	59.97	59.95	59.93	59.91	59.89	59.87	59.85	59.83	59.81	59.79	59.77
0.04						60.12	60.10	60.08	60.06	60.04	60.02	60.00	59.98	59.96	59.94	59.92	59.90	59.88	59.86	59.84	59.82	59.80
0.05							60.13	60.11	60.09	60.07	60.05	60.03	60.01	59.99	59.97	59.95	59.93	59.91	59.89	59.87	59.85	59.83
0.06								60.14	60.12	60.10	60.08	60.06	60.04	60.02	60.00	59.98	59.96	59.94	59.92	59.90	59.88	59.86
0.07									60.15	60.13	60.11	60.09	60.07	60.05	60.03	60.01	59.99	59.97	59.95	59.93	59.91	59.89
0.08										60.16	60.14	60.12	60.10	60.08	60.06	60.04	60.02	60.00	59.98	59.96	59.94	59.92
0.09											60.16	60.14	60.12	60.10	60.08	60.07	60.05	60.03	60.01	59.99	59.97	59.95
0.1												60.17	60.15	60.13	60.11	60.09	60.07	60.05	60.03	60.01	59.99	59.97

Table 1: Mole mass (g/mole) for a $Si_{(1-z)}O_{(2-y)}N_yP_z$ type material with $z \in [0, 0.1]$, $y \in [0, 0.2]$ and $y > z$.

10

Applying the above mentioned intervals, it is possible to calculate the atomic densities of Si, O, P and N when knowing the mass density ($\rho \text{ (g/cm}^3\text{)}$) of the material. However, the mass density is expected to vary with the atomic structure. For a PECVD SiON-type material, a density between 2.26 g/cm^3 and 2.35 g/mole has been measured (cf. Kent Erik Mattsson, Ph.D thesis MIC, The Technical University of Denmark, 1994). For various forms of quartz, densities such as 2.32, 2.19, 2.26, 2.635, 2.13 g/mole can be found in "Handbook of chemistry and Physics" 66TH edition.

15

20

As an illustrative example, the mass density is assumed to be 2.3 g/mole for a $Si_{(1-z)}O_{(2-y)}N_yP_z$ type material with $z \in [0, 0.1]$, $y \in [0, 0.2]$ and $y > z$. The corresponding atomic densities for Si, O, P, and N can be calculated. The resulting values are shown in tables 2, 3, 4, and 5, respectively, wherein 10^{21} is written as 1E21, i.e. e.g. $7.7 \cdot 10^{21}$ is written as 7.7E21.

25

Density of Si atoms/cm3	y
----------------------------	---

z	0	0.01	0.02	0.03	0.04	0.05	0.06	0.07	0.08	0.09	0.1	0.11	0.12	0.13	0.14	0.15	0.16	0.17	0.18	0.19	0.2
0	7.7E21	7.7E21	7.7E21	7.7E21	7.7E21	7.7E21	7.7E21	7.7E21	7.7E21	7.7E21	7.7E21	7.7E21	7.7E21	7.7E21	7.7E21	7.7E21	7.7E21	7.7E21	7.7E21	7.7E21	7.7E21
0.01		7.6E21	7.6E21	7.6E21	7.6E21	7.6E21	7.6E21	7.6E21	7.6E21	7.6E21	7.6E21	7.6E21	7.6E21	7.6E21	7.6E21	7.6E21	7.6E21	7.6E21	7.6E21	7.6E21	7.6E21
0.02			7.5E21	7.5E21	7.5E21	7.5E21	7.5E21	7.5E21	7.5E21	7.5E21	7.5E21	7.5E21	7.5E21	7.5E21	7.5E21	7.5E21	7.5E21	7.5E21	7.5E21	7.5E21	7.5E21
0.03				7.4E21	7.4E21	7.4E21	7.4E21	7.4E21	7.4E21	7.4E21	7.4E21	7.4E21	7.4E21	7.4E21	7.4E21	7.4E21	7.4E21	7.4E21	7.4E21	7.4E21	7.4E21
0.04					7.3E21	7.3E21	7.3E21	7.3E21	7.3E21	7.3E21	7.3E21	7.3E21	7.3E21	7.3E21	7.3E21	7.3E21	7.3E21	7.3E21	7.3E21	7.3E21	7.3E21
0.05						7.2E21	7.2E21	7.2E21	7.2E21	7.2E21	7.2E21	7.2E21	7.2E21	7.2E21	7.2E21	7.2E21	7.2E21	7.2E21	7.2E21	7.2E21	7.2E21
0.06							7.1E21	7.1E21	7.1E21	7.1E21	7.1E21	7.1E21	7.1E21	7.1E21	7.1E21	7.1E21	7.1E21	7.1E21	7.1E21	7.1E21	7.1E21
0.07								7.0E21	7.0E21	7.0E21	7.0E21	7.0E21	7.0E21	7.0E21	7.0E21	7.0E21	7.0E21	7.0E21	7.0E21	7.0E21	7.0E21
0.08									6.9E21	6.9E21	6.9E21	6.9E21	6.9E21	6.9E21	6.9E21	6.9E21	6.9E21	6.9E21	6.9E21	6.9E21	6.9E21
0.09										6.8E21	6.8E21	6.8E21	6.8E21	6.8E21	6.8E21	6.8E21	6.8E21	6.8E21	6.8E21	6.8E21	6.8E21
0.1											6.7E21	6.7E21	6.7E21	6.7E21	6.7E21	6.7E21	6.7E21	6.7E21	6.7E21	6.7E21	6.7E21

Table 2: Atomic density of Si (atoms/cm³) for a Si_(1-z)O_(2-y)N_yP_z type material with $z \in [0, 0.1]$, $y \in [0, 0.2]$ and $y > z$. The mass density is assumed to be 2.3 g/mole.

5

From table 2, it is seen that the density of Si is between 6.9E21 and 7.7E21 atoms/cm³, assuming $\rho = 2.3 \text{ g/cm}^3$.

Density of N atoms/cm ³		y																					
z	0	0.01	0.02	0.03	0.04	0.05	0.06	0.07	0.08	0.09	0.1	0.11	0.12	0.13	0.14	0.15	0.16	0.17	0.18	0.19	0.2		
0	0.0E+00	7.7E19	1.5E20	2.3E20	3.1E20	3.8E20	4.6E20	5.4E20	6.2E20	6.9E20	7.7E20	8.5E20	9.3E20	1.0E21	1.1E21	1.2E21	1.2E21	1.3E21	1.4E21	1.5E21	1.5E21		
0.01		7.7E19	1.5E20	2.3E20	3.1E20	3.8E20	4.6E20	5.4E20	6.2E20	6.9E20	7.7E20	8.5E20	9.3E20	1.0E21	1.1E21	1.2E21	1.2E21	1.3E21	1.4E21	1.5E21	1.5E21		
0.02			1.5E20	2.3E20	3.1E20	3.8E20	4.6E20	5.4E20	6.2E20	6.9E20	7.7E20	8.5E20	9.2E20	1.0E21	1.1E21	1.2E21	1.2E21	1.3E21	1.4E21	1.5E21	1.5E21		
0.03				2.3E20	3.1E20	3.8E20	4.6E20	5.4E20	6.2E20	6.9E20	7.7E20	8.5E20	9.2E20	1.0E21	1.1E21	1.2E21	1.2E21	1.3E21	1.4E21	1.5E21	1.5E21		
0.04					3.1E20	3.8E20	4.6E20	5.4E20	6.2E20	6.9E20	7.7E20	8.5E20	9.2E20	1.0E21	1.1E21	1.2E21	1.2E21	1.3E21	1.4E21	1.5E21	1.5E21		
0.05						3.8E20	4.6E20	5.4E20	6.1E20	6.9E20	7.7E20	8.5E20	9.2E20	1.0E21	1.1E21	1.2E21	1.2E21	1.3E21	1.4E21	1.5E21	1.5E21		
0.06							4.6E20	5.4E20	6.1E20	6.9E20	7.7E20	8.5E20	9.2E20	1.0E21	1.1E21	1.2E21	1.2E21	1.3E21	1.4E21	1.5E21	1.5E21		
0.07								5.4E20	6.1E20	6.9E20	7.7E20	8.5E20	9.2E20	1.0E21	1.1E21	1.2E21	1.2E21	1.3E21	1.4E21	1.5E21	1.5E21		
0.08									6.1E20	6.9E20	7.7E20	8.5E20	9.2E20	1.0E21	1.1E21	1.2E21	1.2E21	1.3E21	1.4E21	1.5E21	1.5E21		
0.09										6.9E20	7.7E20	8.4E20	9.2E20	1.0E21	1.1E21	1.2E21	1.2E21	1.3E21	1.4E21	1.5E21	1.5E21		
0.1											7.7E20	8.4E20	9.2E20	1.0E21	1.1E21	1.2E21	1.2E21	1.3E21	1.4E21	1.5E21	1.5E21		

10

Table 3. Atomic density of N (atoms/cm³) for a Si_(1-z)O_(2-y)N_yP_z type material with $z \in [0, 0.1]$, $y \in [0, 0.2]$ and $y > z$. The mass density is assumed to be 2.3 g/mole.

15 From table 3, it is seen that the density of N is between 0 and 1.5E21 atoms/cm³, assuming $\rho = 2.3 \text{ g/cm}^3$.

Density of P atoms/cm ³		y																					
z	0	0.01	0.02	0.03	0.04	0.05	0.06	0.07	0.08	0.09	0.1	0.11	0.12	0.13	0.14	0.15	0.16	0.17	0.18	0.19	0.2		
0	0.0E00	0.0E00	0.0E00	0.0E00	0.0E00	0.0E00	0.0E00	0.0E00	0.0E00	0.0E00	0.0E00	0.0E00	0.0E00	0.0E00	0.0E00	0.0E00	0.0E00	0.0E00	0.0E00	0.0E00	0.0E00		

[illegible]

Table 4. Atomic density of P (atoms/cm³) for a Si_(1-z)O_(2-y)N_yP_z type material with $z \in [0, 0.1]$, $y \in [0, 0.2]$ and $y > z$. The mass density is assumed to be 2.3 g/mole.

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From table 4, it is seen that the density of P. is between 0 and $7.7\text{E}20$ atoms/ cm^3 , assuming $\rho = 2.3 \text{ g/cm}^3$.

[illegible]

Table 5. Atomic density of O (atoms/cm³) for a Si_(1-z)O_(2-y)N_yP_z type material with $z \in [0, 0.1]$, $y \in [0, 0.2]$ and $y > z$. The mass density is assumed to be 2.3 g/mole.

15 From table 5, it is seen that the density of O is between 1.4E22 and 1.5E22 atoms/cm³, assuming $\rho = 2.3 \text{ g/cm}^3$.

Similar evaluations can be performed for a range of mass densities around 2.3 g/mole. The hereby calculated maximal and minimal atomic densities have been summarized in table 6.

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	Si atoms/	O atoms/	N atoms/	P atoms/
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Massefylde g/cm ³	cm ³		cm ³		cm ³		cm ³	
	min	maks	min	maks	min	maks	min	maks
1.5	4.5E21	5.0E21	9.0E21	1.0E22	0.0E00	1.0E21	0.0E00	5.0E20
1.6	4.8E21	5.4E21	9.6E21	1.1E22	0.0E00	1.1E21	0.0E00	5.4E20
1.7	5.1E21	5.7E21	1.0E22	1.1E22	0.0E00	1.1E21	0.0E00	5.7E20
1.8	5.4E21	6.1E21	1.1E22	1.2E22	0.0E00	1.2E21	0.0E00	6.0E20
1.9	5.7E21	6.4E21	1.1E22	1.3E22	0.0E00	1.3E21	0.0E00	6.4E20
2	6.9E21	7.7E21	1.4E22	1.5E22	0.0E00	1.5E21	0.0E00	7.7E20
2.1	6.3E21	7.1E21	1.3E22	1.4E22	0.0E00	1.4E21	0.0E00	7.0E20
2.2	6.6E21	7.4E21	1.3E22	1.5E22	0.0E00	1.5E21	0.0E00	7.4E20
2.3	6.9E21	7.7E21	1.4E22	1.5E22	0.0E00	1.5E21	0.0E00	7.7E20
2.4	7.2E21	8.1E21	1.4E22	1.6E22	0.0E00	1.6E21	0.0E00	8.0E20
2.5	7.5E21	8.4E21	1.5E22	1.7E22	0.0E00	1.7E21	0.0E00	8.4E20
2.6	7.8E21	8.7E21	1.6E22	1.7E22	0.0E00	1.7E21	0.0E00	8.7E20
2.7	8.1E21	9.1E21	1.6E22	1.8E22	0.0E00	1.8E21	0.0E00	9.0E20
2.8	8.4E21	9.4E21	1.7E22	1.9E22	0.0E00	1.9E21	0.0E00	9.4E20
2.9	8.7E21	9.8E21	1.7E22	1.9E22	0.0E00	2.0E21	0.0E00	9.7E20
3	9.0E21	1.0E22	1.8E22	2.0E22	0.0E00	2.0E21	0.0E00	1.0E21
3.1	9.3E21	1.0E22	1.9E22	2.1E22	0.0E00	2.1E21	0.0E00	1.0E21
3.2	9.6E21	1.1E22	1.9E22	2.1E22	0.0E00	2.2E21	0.0E00	1.1E21
3.3	9.9E21	1.1E22	2.0E22	2.2E22	0.0E00	2.2E21	0.0E00	1.1E21
3.4	1.0E22	1.1E22	2.0E22	2.3E22	0.0E00	2.3E21	0.0E00	1.1E21
3.5	1.0E22	1.2E22	2.1E22	2.3E22	0.0E00	2.4E21	0.0E00	1.2E21
3.6	1.1E22	1.2E22	2.2E22	2.4E22	0.0E00	2.4E21	0.0E00	1.2E21
3.7	1.1E22	1.2E22	2.2E22	2.5E22	0.0E00	2.5E21	0.0E00	1.2E21
3.8	1.1E22	1.3E22	2.3E22	2.5E22	0.0E00	2.6E21	0.0E00	1.3E21
3.9	1.2E22	1.3E22	2.3E22	2.6E22	0.0E00	2.6E21	0.0E00	1.3E21
4	1.2E22	1.3E22	2.4E22	2.7E22	0.0E00	2.7E21	0.0E00	1.3E21

Table 6. Mass densities between 1.5 and 4 g/mole and the hereby maximum and minimum number of atoms per cm³ assuming a Si_(1-z)O_(2-y)N_yP_z type material with $z \in [0, 0.1]$, $y \in [0, 0.2]$ and $y > z$.

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Based on table 6 one can state that for a Si_(1-z)O_(2-y)N_yP_z type material with $z \in [0, 0.1]$, $y \in [0, 0.2]$ and $y > z$ with a mass density between 1.5 and 4 g/cm³ the atomic densities of Si, O, N and P will be in the ranges indicated below:

- 10 The atomic density of Si is between 4.5E21 and 1.3E22 atoms/cm³.
The atomic density of O is between 9.0E21 and 2.7E22 atoms/cm³.
The atomic density of N is between 0 and 2.7E21 atoms/cm³.
The atomic density of P is between 0 and 1.3E21 atoms/cm³.

In an embodiment of the invention (EXAMPLE 1), the density of N and P was determined to $[N] = 1.30E21$ atoms/cm³ and $[P] = 4.58E20$ atoms/cm³ which is within the above mentioned ranges for N and P.

- 5 FIG. 6 shows a schematic (x-y-plane) cross sectional view of an optical component 100 according to the invention comprising a base (or lower cladding) layer 61 formed on a substrate 10 with various waveguide core elements 31, 32, 33 applied to the base layer and covered by an upper cladding layer 62 (the combined cladding layers 61, 62 being denoted 6 in
10 FIG. 6). The upper cladding layer has an upper surface 621, possibly being corrugated (although not to scale in FIG. 6) due to an anneal and reflow procedure. Waveguides 31, 32, 33 of different widths w_1 , w_2 , w_3 , respectively, and identical height h (equal to the thickness of the core layer) are shown. The waveguides have end facets 331 (assuming that the cross
15 section of FIG. 6 is an 'end view' of a component). The substrate (e.g. a silicon substrate) 10 has a bottom essentially planar face 11 (x-z-plane).

The invention is defined by the features of the independent claim(s). Preferred embodiments are defined in the dependent claims.

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Some preferred embodiments have been shown in the foregoing, but it should be stressed that the invention is not limited to these, but may be embodied in other ways within the subject-matter defined in the following claims.

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